Yasuo Koide

List of Publications by Year
in descending order

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293 papers	10,947 citations	34105 52 h-index	38395 95 g-index
298 all docs	298 docs citations	298 times ranked	9450 citing authors

#	Article	IF	Citations
1	Effects of ain buffer layer on crystallographic structure and on electrical and optical properties of GaN and Ga1â^'xAlxN (0 < x â‰¦ 0.4) films grown on sapphire substrate by MOVPE. Journal of Crystal Growth, 1989, 98, 209-219.	1.5	689
2	Singleâ€Crystalline ZnS Nanobelts as Ultravioletâ€Light Sensors. Advanced Materials, 2009, 21, 2034-2039.	21.0	537
3	Centimeterâ€Long V₂O₅ Nanowires: From Synthesis to Fieldâ€Emission, Electrochemical, Electrical Transport, and Photoconductive Properties. Advanced Materials, 2010, 22, 2547-2552.	21.0	359
4	Singleâ€Crystalline CdS Nanobelts for Excellent Fieldâ€Emitters and Ultrahigh Quantumâ€Efficiency Photodetectors. Advanced Materials, 2010, 22, 3161-3165.	21.0	342
5	Efficient Assembly of Bridged <i>Î²</i>â€Ga₂O₃ Nanowires for Solarâ€Blind Photodetection. Advanced Functional Materials, 2010, 20, 3972-3978.	14.9	292
6	Fabrication of High-Quality In₂Se₃ Nanowire Arrays toward High-Performance Visible-Light Photodetectors. ACS Nano, 2010, 4, 1596-1602.	14.6	289
7	Flexible Ultraviolet Photodetectors with Broad Photoresponse Based on Branched ZnSâ€ZnO Heterostructure Nanofilms. Advanced Materials, 2014, 26, 3088-3093.	21.0	251
8	Ultrahighâ€Performance Solarâ€Blind Photodetectors Based on Individual Singleâ€crystalline In₂Ge₂O₇ Nanobelts. Advanced Materials, 2010, 22, 5145-5149.	21.0	249
9	An Efficient Way to Assemble ZnS Nanobelts as Ultravioletâ€Light Sensors with Enhanced Photocurrent and Stability. Advanced Functional Materials, 2010, 20, 500-508.	14.9	222
10	Highâ€Performance Blue/Ultravioletâ€Lightâ€Sensitive ZnSeâ€Nanobelt Photodetectors. Advanced Materials, 2009, 21, 5016-5021.	21.0	217
11	Effects of surface treatments and metal work functions on electrical properties atp-GaN/metal interfaces. Journal of Applied Physics, 1997, 81, 1315-1322.	2.5	213
12	Deep-ultraviolet solar-blind photoconductivity of individual gallium oxide nanobelts. Nanoscale, 2011, 3, 1120.	5.6	210
13	Polarization independent visible color filter comprising an aluminum film with surface-plasmon enhanced transmission through a subwavelength array of holes. Applied Physics Letters, 2011, 98, .	3.3	208
14	Energy bandâ€gap bowing parameter in an AlxGa1â^'xN alloy. Journal of Applied Physics, 1987, 61, 4540-4543.	2.5	194
15	Electrical Transport and Highâ€Performance Photoconductivity in Individual ZrS₂ Nanobelts. Advanced Materials, 2010, 22, 4151-4156.	21.0	169
16	Extreme dielectric strength in boron doped homoepitaxial diamond. Applied Physics Letters, 2010, 97, .	3.3	160
17	Singleâ€Crystalline Sb₂Se₃ Nanowires for Highâ€Performance Field Emitters and Photodetectors. Advanced Materials, 2010, 22, 4530-4533.	21.0	147
18	Effects of annealing in an oxygen ambient on electrical properties of ohmic contacts to p-type GaN. Journal of Electronic Materials, 1999, 28, 341-346.	2.2	133

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19	High-performance metal-semiconductor-metal deep-ultraviolet photodetectors based on homoepitaxial diamond thin film. Applied Physics Letters, 2006, 89, 113509.	3.3	121
20	Low on-resistance diamond field effect transistor with high-k ZrO2 as dielectric. Scientific Reports, 2014, 4, 6395.	3.3	107
21	Effect of AlN Buffer Layer on AlGaN/Î±-Al2O3Heteroepitaxial Growth by Metalorganic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 1988, 27, 1156-1161.	1.5	105
22	Normally-off HfO2-gated diamond field effect transistors. Applied Physics Letters, 2013, 103, .	3.3	105
23	WO3 nanowires on carbon papers: electronic transport, improved ultraviolet-light photodetectors and excellent field emitters. Journal of Materials Chemistry, 2011, 21, 6525.	6.7	103
24	Suspended Singleâ€Crystal Diamond Nanowires for Highâ€Performance Nanoelectromechanical Switches. Advanced Materials, 2010, 22, 5393-5397.	21.0	101
25	Single Schottky-barrier photodiode with interdigitated-finger geometry: Application to diamond. Applied Physics Letters, 2007, 90, 123507.	3.3	96
26	Thermally stable visible-blind diamond photodiode using tungsten carbide Schottky contact. Applied Physics Letters, 2005, 87, 022105.	3.3	94
27	Low contact resistance metals for graphene based devices. Diamond and Related Materials, 2012, 24, 171-174.	3.9	94
28	Visible-blind deep-ultraviolet Schottky photodetector with a photocurrent gain based on individual Zn2GeO4 nanowire. Applied Physics Letters, 2010, 97, .	3.3	89
29	Conduction Mechanism of Leakage Current in Ta2â€‰Oâ€‰5 Films on Si Prepared by LPCVD. Journal of the Electrochemical Society, 1990, 137, 2876-2879.	2.9	84
30	Epitaxial Growth and Properties of Al x Ga1â€‰âˆ'â€‰x â€‰Nâ€‰ by MOVPE. Journal of the Electrochemical Society, 1986, 133, 1956-1960.	2.9	82
31	Light intensity dependence of photocurrent gain in single-crystal diamond detectors. Physical Review B, 2010, 81, .	3.2	81
32	Band offsets of Al2O3 and HfO2 oxides deposited by atomic layer deposition technique on hydrogenated diamond. Applied Physics Letters, 2012, 101, .	3.3	76
33	Persistent positive and transient absolute negative photoconductivity observed in diamond photodetectors. Physical Review B, 2008, 78, .	3.2	75
34	Solidâ€phase reactions and crystallographic structures in Zr/Si systems. Journal of Applied Physics, 1991, 69, 7050-7056.	2.5	74
35	Edge emission of AlxGa1âˆ'xN. Solid State Communications, 1986, 60, 509-512.	1.9	73
36	Effects of NiO on electrical properties of NiAu-based ohmic contacts for p-type GaN. Applied Physics Letters, 1999, 75, 4145-4147.	3.3	73

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37	Development of Ni/Al and Ni/Ti/Al ohmic contact materials for p-type 4H-SiC. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 98, 286-293.	3.5	72
38	Low-leakage p-type diamond Schottky diodes prepared using vacuum ultraviolet light/ozone treatment. Journal of Applied Physics, 2009, 105, .	2.5	71
39	Thermally stable solar-blind diamond UV photodetector. Diamond and Related Materials, 2006, 15, 1962-1966.	3.9	69
40	Homoepitaxial diamond film growth: High purity, high crystalline quality, isotopic enrichment, and single color center formation. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 2365-2384.	1.8	68
41	Low-resistance Ta/Ti Ohmic contacts for p-type GaN. Applied Physics Letters, 1999, 74, 275-277.	3.3	67
42	Ohmic Contacts for Compound Semiconductors. Critical Reviews in Solid State and Materials Sciences, 1998, 23, 1-60.	12.3	64
43	An Interface Engineered Multicolor Photodetector Based on nâ€Si(111)/TiO₂ Nanorod Array Heterojunction. Advanced Functional Materials, 2016, 26, 1400-1410.	14.9	64
44	Enhancement-mode hydrogenated diamond metal-oxide-semiconductor field-effect transistors with Y2O3 oxide insulator grown by electron beam evaporator. Applied Physics Letters, 2017, 110, .	3.3	64
45	Enhanced performance of InGaN solar cell by using a super-thin AlN interlayer. Applied Physics Letters, 2011, 99, .	3.3	62
46	High-temperature ultraviolet detection based on InGaN Schottky photodiodes. Applied Physics Letters, 2011, 99, .	3.3	61
47	Interfacial band configuration and electrical properties of LaAlO3/Al2O3/hydrogenated-diamond metal-oxide-semiconductor field effect transistors. Journal of Applied Physics, 2013, 114, .	2.5	60
48	Comprehensive Investigation of Single Crystal Diamond Deep-Ultraviolet Detectors. Japanese Journal of Applied Physics, 2012, 51, 090115.	1.5	60
49	Carrier transport mechanism of Ohmic contact to p-type diamond. Journal of Applied Physics, 1997, 81, 6815-6821.	2.5	59
50	High-performance metal-semiconductor-metal InGaN photodetectors using CaF2 as the insulator. Applied Physics Letters, 2011, 98, 103502.	3.3	56
51	Carbon-Based Materials: Growth, Properties, MEMS/NEMS Technologies, and MEM/NEM Switches. Critical Reviews in Solid State and Materials Sciences, 2011, 36, 66-101.	12.3	55
52	Initial leakage current paths in the vertical-type GaN-on-GaN Schottky barrier diodes. Applied Physics Letters, 2017, 111, .	3.3	55
53	Morphology-tunable In2Se3 nanostructures with enhanced electrical and photoelectrical performances via sulfur doping. Journal of Materials Chemistry, 2010, 20, 6630.	6.7	54
54	Effects of sp2/sp3 bonding ratios on field emission properties of diamond-like carbon films grown by microwave plasma chemical vapor deposition. Diamond and Related Materials, 2002, 11, 1429-1435.	3.9	51

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55	Initial Stage of Growth of Ge on (100)Si by Gas Source Molecular Beam Epitaxy Using GeH4. Japanese Journal of Applied Physics, 1989, 28, L690-L693.	1.5	50
56	Doping and interface of homoepitaxial diamond for electronic applications. MRS Bulletin, 2014, 39, 499-503.	3.5	49
57	Logic Circuits With Hydrogenated Diamond Field-Effect Transistors. IEEE Electron Device Letters, 2017, 38, 922-925.	3.9	49
58	Mechanisms of silicon oxidation at low temperatures by microwaveâ€excited O2gas and O2â€N2mixed gas. Journal of Applied Physics, 1990, 67, 2603-2607.	2.5	46
59	Non-destructive detection of killer defects of diamond Schottky barrier diodes. Journal of Applied Physics, 2011, 110, .	2.5	44
60	Low Resistance TiAl Ohmic Contacts with Multi-Layered Structure for p-Type 4H-SiC. Materials Transactions, 2002, 43, 1684-1688.	1.2	43
61	Photovoltaic Schottky ultraviolet detectors fabricated on boron-doped homoepitaxial diamond layer. Applied Physics Letters, 2006, 88, 033504.	3.3	43
62	Comprehensive Investigation of Single Crystal Diamond Deep-Ultraviolet Detectors. Japanese Journal of Applied Physics, 2012, 51, 090115.	1.5	43
63	Electrical characteristics of hydrogen-terminated diamond metal-oxide-semiconductor with atomic layer deposited HfO2 as gate dielectric. Applied Physics Letters, 2013, 102, .	3.3	42
64	Deposition of TiO2/Al2O3 bilayer on hydrogenated diamond for electronic devices: Capacitors, field-effect transistors, and logic inverters. Journal of Applied Physics, 2017, 121, .	2.5	42
65	Electric Field Breakdown of Lateral Schottky Diodes of Diamond. Japanese Journal of Applied Physics, 2007, 46, L196-L198.	1.5	41
66	Integration of high-dielectric constant Ta2O5 oxides on diamond for power devices. Applied Physics Letters, 2012, 101, .	3.3	41
67	Arbitrary Multicolor Photodetection by Hetero-integrated Semiconductor Nanostructures. Scientific Reports, 2013, 3, 2368.	3.3	41
68	A Multilevel Intermediateâ€Band Solar Cell by InGaN/GaN Quantum Dots with a Strainâ€Modulated Structure. Advanced Materials, 2014, 26, 1414-1420.	21.0	40
69	Growth processes in the initial stages of deposition of Ge films on (100) Si surfaces by GeH4 source molecular beam epitaxy. Journal of Crystal Growth, 1990, 99, 254-258.	1.5	39
70	Demonstration of diamond field effect transistors by AlN/diamond heterostructure. Physica Status Solidi - Rapid Research Letters, 2011, 5, 125-127.	2.4	39
71	Energyâ€Efficient Metalâ€"Insulatorâ€"Metalâ€Semiconductor Fieldâ€Effect Transistors Based on 2D Carrier Gases. Advanced Electronic Materials, 2019, 5, 1800832.	5.1	39
72	Thermal Stability of Diamond Photodiodes Using Tungsten Carbide as Schottky Contact. Japanese Journal of Applied Physics, 2005, 44, 7832-7838.	1.5	38

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73	Bascule nanobridges self-assembled with ZnO nanowires as double Schottky barrier UV switches. Nanotechnology, 2010, 21, 295502.	2.6	38
74	P-Channel InGaN/GaN heterostructure metal-oxide-semiconductor field effect transistor based on polarization-induced two-dimensional hole gas. Scientific Reports, 2016, 6, 23683.	3.3	37
75	Design and fabrication of high-performance diamond triple-gate field-effect transistors. Scientific Reports, 2016, 6, 34757.	3.3	37
76	Highâ€temperature stability of Au/pâ€type diamond Schottky diode. Physica Status Solidi - Rapid Research Letters, 2009, 3, 211-213.	2.4	36
77	Batch production of single-crystal diamond bridges and cantilevers for microelectromechanical systems. Journal of Micromechanics and Microengineering, 2010, 20, 085002.	2.6	36
78	Nearly ideal vertical GaN Schottky barrier diodes with ultralow turn-on voltage and on-resistance. Applied Physics Express, 2017, 10, 051001.	2.4	36
79	Effect of Pd or Pt addition to Ti/Al ohmic contact materials for n-type AlGaN. Applied Physics Letters, 2002, 80, 2934-2936.	3.3	35
80	Control of normally on/off characteristics in hydrogenated diamond metal-insulator-semiconductor field-effect transistors. Journal of Applied Physics, 2015, 118, .	2.5	35
81	Dependence of electrical properties on work functions of metals contacting to p-type GaN. Applied Surface Science, 1997, 117-118, 373-379.	6.1	33
82	Development of AlN/diamond heterojunction field effect transistors. Diamond and Related Materials, 2012, 24, 206-209.	3.9	31
83	Diamond field effect transistors with a high-dielectric constant Ta₂O₅as gate material. Journal Physics D: Applied Physics, 2014, 47, 245102.	2.8	31
84	Effects of oxidation conditions on electrical properties of SiCâ€SiO2interfaces. Journal of Applied Physics, 1990, 68, 6304-6308.	2.5	29
85	Study on determining factors of low contact resistivity in transition metal-silicon systems. Applied Surface Science, 1993, 70-71, 624-628.	6.1	29
86	Sb2O3nanobelt networks for excellent visible-light-range photodetectors. Nanotechnology, 2011, 22, 165704.	2.6	29
87	Diamond logic inverter with enhancement-mode metal-insulator-semiconductor field effect transistor. Applied Physics Letters, 2014, 105, .	3.3	29
88	Large deep-ultraviolet photocurrent in metal-semiconductor-metal structures fabricated on as-grown boron-doped diamond. Applied Physics Letters, 2005, 87, 113507.	3.3	28
89	Electron microscopy studies of the intermediate layers at the SiO₂/GaN interface. Japanese Journal of Applied Physics, 2017, 56, 110312.	1.5	28
90	Observation of an ordered structure in the initial stage of Ge/Si heteroepitaxial growth. Applied Physics Letters, 1990, 57, 2434-2436.	3.3	27

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91	Energy dissipation in micron- and submicron-thick single crystal diamond mechanical resonators. Applied Physics Letters, 2014, 105, .	3.3	26
92	InGaN-based thin film solar cells: Epitaxy, structural design, and photovoltaic properties. Journal of Applied Physics, 2015, 117, .	2.5	26
93	Assembly of a high-dielectric constant thin TiOx layer directly on H-terminated semiconductor diamond. Applied Physics Letters, 2016, 108, .	3.3	26
94	Improvement of the quality factor of single crystal diamond mechanical resonators. Japanese Journal of Applied Physics, 2017, 56, 024101.	1.5	26
95	Interface trap characterization of Al2O3/GaN vertical-type MOS capacitors on GaN substrate with surface treatments. Journal of Alloys and Compounds, 2018, 767, 600-605.	5.5	26
96	Single-crystal diamond microelectromechanical resonator integrated with a magneto-strictive galfenol film for magnetic sensing. Carbon, 2019, 152, 788-795.	10.3	26
97	Simultaneous observation of luminescence and dissociation processes of Mgâ€“H complex for Mg-doped GaN. Journal of Applied Physics, 2002, 92, 3657-3661.	2.5	25
98	High-<i>k</i> ZrO2/Al2O3 bilayer on hydrogenated diamond: Band configuration, breakdown field, and electrical properties of field-effect transistors. Journal of Applied Physics, 2016, 120, .	2.5	25
99	Ultrahigh Performance Onâ€Chip Single Crystal Diamond NEMS/MEMS with Electrically Tailored Selfâ€Sensing Enhancing Actuation. Advanced Materials Technologies, 2019, 4, 1800325.	5.8	25
100	Photoelectron spectroscopic studies on interfacial reactions in Zr/2Ã—1(100)Si and Zr/SiO2/(100)Si systems. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1993, 11, 2619-2622.	2.1	24
101	Development of Pt-based ohmic contact materials for p-type GaN. Journal of Applied Physics, 2001, 89, 2826-2831.	2.5	24
102	Ohmic contact for p-type diamond without postannealing. Journal of Applied Physics, 2008, 104, 016104.	2.5	24
103	Growth mechanism of c-axis-oriented AlN on (0 0 1) diamond substrates by metal-organic vapor phase epitaxy. Journal of Crystal Growth, 2010, 312, 368-372.	1.5	24
104	Effective Use of Source Gas for Diamond Growth with Isotopic Enrichment. Applied Physics Express, 2013, 6, 055601.	2.4	24
105	Enhancing Delta <i>E</i> Effect at High Temperatures of Galfenol/Ti/Single-Crystal Diamond Resonators for Magnetic Sensing. ACS Applied Materials & Interfaces, 2020, 12, 23155-23164.	8.0	24
106	Relationship between growth processes and strain relaxation in Si1âˆ’xGexfilms grown on (100)Siâ€(2Ã—1) surfaces by gas source molecular beam epitaxy. Journal of Applied Physics, 1993, 73, 2288-2293.	2.5	23
107	Growth mechanism of c-axis-oriented AlN on (1 1 1) diamond substrates by metal-organic vapor phase epitaxy. Journal of Crystal Growth, 2010, 312, 1325-1328.	1.5	23
108	Mechanism of reverse current increase of vertical-type diamond Schottky diodes. Journal of Applied Physics, 2017, 122, .	2.5	23

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109	Solid phase reaction and electrical properties in Zr/Si system. Applied Physics Letters, 1990, 57, 1105-1107.	3.3	22
110	Structural properties and transfer characteristics of sputter deposition AlN and atomic layer deposition Al2O3 bilayer gate materials for H-terminated diamond field effect transistors. Journal of Applied Physics, 2016, 120, .	2.5	22
111	Boosting the doping efficiency of Mg in <i>p</i>-GaN grown on the free-standing GaN substrates. Applied Physics Letters, 2019, 115, .	3.3	22
112	Controlled formation of wrinkled diamond-like carbon (DLC) film on grooved poly(dimethylsiloxane) substrate. Diamond and Related Materials, 2012, 22, 48-51.	3.9	21
113	Electrical properties of atomic layer deposited HfO2/Al2O3 multilayer on diamond. Diamond and Related Materials, 2015, 54, 55-58.	3.9	21
114	Comparative Analysis of Defects in Mg-Implanted and Mg-Doped GaN Layers on Freestanding GaN Substrates. Nanoscale Research Letters, 2018, 13, 403.	5.7	21
115	Schottky barrier height and thermal stability of p-diamond (100) Schottky interfaces. Thin Solid Films, 2014, 557, 241-248.	1.8	20
116	Magnetic Control of Magneto-Electrochemical Cell and Electric Double Layer Transistor. Scientific Reports, 2017, 7, 10534.	3.3	20
117	Influence of post-deposition annealing on characteristics of Pt/Al2O3/Î²-Ga2O3 MOS capacitors. Microelectronic Engineering, 2019, 216, 111040.	2.4	20
118	Diamond Schottky diodes with ideality factors close to 1. Applied Physics Letters, 2014, 105, 133515.	3.3	19
119	Electrical hysteresis in p-GaN metalâ€“oxideâ€“semiconductor capacitor with atomic-layer-deposited Al₂O₃ as gate dielectric. Applied Physics Express, 2016, 9, 121002.	2.4	19
120	Layered boron nitride enabling high-performance AlGaN/GaN high electron mobility transistor. Journal of Alloys and Compounds, 2020, 829, 154542.	5.5	19
121	Coupling of magneto-strictive FeGa film with single-crystal diamond MEMS resonator for high-reliability magnetic sensing at high temperatures. Materials Research Letters, 2020, 8, 180-186.	8.7	19
122	Growth processes in the initial stage of Ge films on (811)Si surfaces by GeH4source molecular beam epitaxy. Journal of Applied Physics, 1990, 68, 2164-2167.	2.5	18
123	In-situ RHEED study of growth processes in the initial stage of SiGe alloy film deposition by gas source molecular beam epitaxy. Journal of Crystal Growth, 1991, 115, 365-370.	1.5	18
124	High-detectivity nanowire photodetectors governed by bulk photocurrent dynamics with thermally stable carbide contacts. Nanotechnology, 2013, 24, 495701.	2.6	18
125	Vertical-Type Ni/GaN UV Photodetectors Fabricated on Free-Standing GaN Substrates. Applied Sciences (Switzerland), 2019, 9, 2895.	2.5	18
126	Enhanced magnetic sensing performance of diamond MEMS magnetic sensor with boron-doped FeGa film. Carbon, 2020, 170, 294-301.	10.3	18

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127	Fixed charges investigation in Al2O3/hydrogenated-diamond metal-oxide-semiconductor capacitors. Applied Physics Letters, 2020, 117, .	3.3	18
128	Metalâ€"diamond semiconductor interface and photodiode application. Applied Surface Science, 2008, 254, 6268-6272.	6.1	17
129	Integration of (PbZr0.52Ti0.48O3) on single crystal diamond as metal-ferroelectric-insulator-semiconductor capacitor. Applied Physics Letters, 2009, 94, .	3.3	17
130	Systematic investigation of surface and bulk electronic structure of undoped In-polar InN epilayers by hard X-ray photoelectron spectroscopy. Journal of Applied Physics, 2013, 114, .	2.5	17
131	Suppression in the electrical hysteresis by using CaF2 dielectric layer for p-GaN MIS capacitors. Journal of Applied Physics, 2018, 123, .	2.5	17
132	High Output Current Boron-Doped Diamond Metal-Semiconductor Field-Effect Transistors. IEEE Electron Device Letters, 2019, 40, 1748-1751.	3.9	17
133	Investigation of Al2O3/GaN interface properties by sub-bandgap photo-assisted capacitance-voltage technique. AIP Advances, 2019, 9, .	1.3	17
134	Characteristics of Al₂O₃/native oxide/n-GaN capacitors by post-metallization annealing. Semiconductor Science and Technology, 2019, 34, 034001.	2.0	17
135	Temperature dependence of Young's modulus of single-crystal diamond determined by dynamic resonance. Diamond and Related Materials, 2021, 116, 108403.	3.9	17
136	Reducing intrinsic energy dissipation in diamond-on-diamond mechanical resonators toward one million quality factor. Physical Review Materials, 2018, 2, .	2.4	17
137	Effects of surface cleaning on electrical properties for Ni contacts to p-type ZnSe. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 1812.	1.6	16
138	Carrier transport mechanisms through the metal/p-type diamond semiconductor interface. Diamond and Related Materials, 1997, 6, 847-851.	3.9	16
139	pâ€type diamond Schottky diodes fabricated by vacuum ultraviolet light/ozone surface oxidation: Comparison with diodes based on wetâ€chemical oxidation. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 2082-2085.	1.8	16
140	Impedance analysis of Al2O3/H-terminated diamond metal-oxide-semiconductor structures. Applied Physics Letters, 2015, 106, 083506.	3.3	16
141	Effect of off-cut angle of hydrogen-terminated diamond(111) substrate on the quality of AlN towards high-density AlN/diamond(111) interface hole channel. Journal of Applied Physics, 2017, 121, .	2.5	16
142	Low-energy ion scattering spectroscopy and reflection high-energy electron diffraction of native oxides on GaN(0001). Japanese Journal of Applied Physics, 2017, 56, 128004.	1.5	16
143	Vaporâ€Phase Etching of InP Using Anhydrous HCl and â€‰PHâ€‰3 Gas. Journal of the Electrochemical Society, 1986, 133, 2204-2205.	2.9	15
144	Schottky barrier heights of metals contacting to p-ZnSe. Journal of Applied Physics, 1997, 82, 2393-2399.	2.5	15

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145	Annealing effects on hydrogenated diamond NOR logic circuits. Applied Physics Letters, 2018, 112, .	3.3	15
146	Effect of Boron Incorporation on Structural and Optical Properties of AlN Layers Grown by Metalâ€Organic Vapor Phase Epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1800282.	1.8	15
147	The electric double layer effect and its strong suppression at Li+ solid electrolyte/hydrogenated diamond interfaces. Communications Chemistry, 2021, 4, .	4.5	15
148	Formation of a superstructure in the initial stage of Ge epitaxial growth on Si(100) substrates. Applied Surface Science, 1991, 48-49, 69-75.	6.1	14
149	Dependence of Electrical Properties on Work Functions of Metals Contacting to p-type ZnSe. Japanese Journal of Applied Physics, 1996, 35, 1657-1663.	1.5	14
150	Crystallographic and electrical characterization of tungsten carbide thin films for Schottky contact of diamond photodiode. Journal of Vacuum Science & Technology B, 2006, 24, 185.	1.3	14
151	Schottky-barrier photodiode using p-diamond epilayer grown on p+-diamond substrates. Diamond and Related Materials, 2009, 18, 296-298.	3.9	14
152	High-performance visible to near-infrared photodetectors by using (Cd,Zn)Te single crystal. Optics Express, 2019, 27, 8935.	3.4	14
153	Peculiarity of Depletion Region in Diamond pn-Junction. Japanese Journal of Applied Physics, 2003, 42, 6800-6803.	1.5	13
154	Electrical characterization of Schottky diodes based on boron doped homoepitaxial diamond films by conducting probe atomic force microscopy. Superlattices and Microstructures, 2006, 40, 343-349.	3.1	13
155	Submicron metal-semiconductor-metal diamond photodiodes toward improving the responsivity. Applied Physics Letters, 2007, 91, 163510.	3.3	13
156	Chemical Vapor Deposition of ¹²C Isotopically Enriched Polycrystalline Diamond. Japanese Journal of Applied Physics, 2012, 51, 090104.	1.5	13
157	Nanoelectromechanical switch fabricated from single crystal diamond: Experiments and modeling. Diamond and Related Materials, 2012, 24, 69-73.	3.9	13
158	Operations of hydrogenated diamond metalâ€"oxideâ€"semiconductor field-effect transistors after annealing at 500 Â°C. Journal Physics D: Applied Physics, 2019, 52, 315104.	2.8	13
159	Epitaxial Combination of Two-Dimensional Hexagonal Boron Nitride with Single-Crystalline Diamond Substrate. ACS Applied Materials & Interfaces, 2020, 12, 46466-46475.	8.0	13
160	NiGe-based ohmic contacts to n-type GaAs. Journal of Electronic Materials, 1996, 25, 1684-1694.	2.2	12
161	Electric field breakdown of lateral-type Schottky diodes formed on lightly doped homoepitaxial diamond. Applied Surface Science, 2008, 254, 6273-6276.	6.1	12
162	Schottky photodiode using submicron thick diamond epilayer for flame sensing. Nano-Micro Letters, 2009, 1, 30-33.	27.0	12

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163	Improved ferroelectric properties of Pb(Zr0.52,Ti0.48)O3 thin film on single crystal diamond using CaF2 layer. Applied Physics Letters, 2010, 96, .	3.3	12
164	Amorphous silicon diamond based heterojunctions with high rectification ratio. Journal of Non-Crystalline Solids, 2012, 358, 2110-2113.	3.1	12
165	Localized mid-gap-states limited reverse current of diamond Schottky diodes. Journal of Applied Physics, 2012, 111, 104503.	2.5	12
166	Spectrally dependent photovoltages in Schottky photodiode based on (100) B-doped diamond. Journal of Applied Physics, 2014, 115, 053105.	2.5	12
167	An Overview of High-k Oxides on Hydrogenated-Diamond for Metal-Oxide-Semiconductor Capacitors and Field-Effect Transistors. Sensors, 2018, 18, 1813.	3.8	12
168	Yâ€Baâ€Cuâ€O superconducting thin films prepared by plasmaâ€assisted flash evaporation. Applied Physics Letters, 1989, 55, 307-309.	3.3	11
169	Formation and deterioration mechanisms of low-resistance TaTi ohmic contacts forp-GaN. Journal of Applied Physics, 1999, 86, 5079-5084.	2.5	11
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